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## **Advanced approach for parameterization of the current generation centers in irradiated silicon sensors**

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An effective approach for evaluating the scenario of Si sensor radiation degradation requires parametrization of the bulk current generation and the electric field transformation in the irradiated sensors. The presented data show that the I-V characteristics of Si sensors damaged by short-range particles allow a reliable differentiating between these processes and defining the parameters of the effective radiation defects including their type and microscopic parameters, which control independently the generated current and the electric field.

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